(19) World Intellectual Property Organization

International Bureau





PC PC

(43) International Publication Date 2 November 2006 (02.11.2006)

(51) International Patent Classification: *H01L 21/336* (2006.01) *H01L 29/76* (2006.01)

(21) International Application Number:

PCT/US2006/015310

(22) International Filing Date: 21 April 2006 (21.04.2006)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:

60/673,935 22 April 2005 (22.04.2005) US

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(10) International Publication Number WO 2006/116219 A1

- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

- with international search report
- before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.



(57) Abstract: A method of manufacturing a semiconductor device includes providing semiconductor substrate having trenches and mesas. At least one mesa has first and second sidewalls. The method includes doping with a dopant of a second conductivity the first sidewall of the mesa, and doping with a dopant of a second conductivity the second sidewall of the mesa. A dopant of the first conductivity is then used to dope the first sidewall of the mesa, and the dopant of the first conductivity is used to dope the second sidewall of the at least one mesa. At least the trenches adjacent to the at least one mesa are then lined with an oxide material and are then filled with one of a semi-insulating material and an insulating material.

